none | none | none

PN - JP7074285 A 19950317

PD - 1995-03-17

PR - JP19940067127 19940405; JP19930080504 19930407

OPD - 1993-04-07

TI - SEMICONDUCTOR DEVICE

IN - YANAGIHARA MANABU;INOUE KAORU;ITO JUNJI;UNO TOMOAKI; ISHIKAWA OSAMU;OTA TOSHIMICHI;SAKAI HIROYUKI

PA - MATSUSHITA ELECTRIC IND CO LTD

IC - H01L23/12 ; H01L21/60 ; H01P3/08 ; H03F3/60

CT - JP5037207 A [ ]; JP4273196 A [ ]

TI - High frequency semiconductor integrated circuit for millimetre wave band - has microstrip wiring board with dielectric film extending on ground conductor and metal wiring line extending on dielectric film

PR - JP19930080504 19930407;JP19930192166 19930803;JP19930328236 19931224

PN - JP7074285 A 19950317 DW199520 H01L23/12 012pp
- US5510758 A 19960423 DW199622 H01P3/08 026pp

PA - (MATU) MATSUSHITA DENKI SANGYO KK
- (MATU) MATSUSHITA ELEC IND CO LTD

IC - H01L21/58 ;H01L21/60 ;H01L23/12 ;H01P3/08 ;H03F3/60

IN - FUJITA S; INOUE K; OTA Y; SAGAWA M; SAKAI H; TAKAHASHI K

AB - J07074285 The device has a silicon or glass substrate provided with a contact hole (15) through which a grounding conductor (10) is connected to a microstrip wiring pattern (12-14). An interlayer insulating film (11) is placed between the wiring pattern and the grounding conductor.
- The semiconductor chip (2) which contains the high frequency transistor is mounted onto the wiring pattern by means of solder bumps (40). The wiring pattern is supported by a lead frame (3).
- ADVANTAGE - High frequency transistor allows device at cut-off frequency of 100 GHz. Allows high density mounting.
- (Dwg.1/13)

OPD - 1993-04-07

AN - 1995-150504 [23]

PN - JP7074285 A 19950317

none | none | none

none	none	none

PD - 1995-03-17

AP - JP19940067127 19940405

IN - SAKAI HIROYUKI; others:06

PA - MATSUSHITA ELECTRIC IND CO LTD

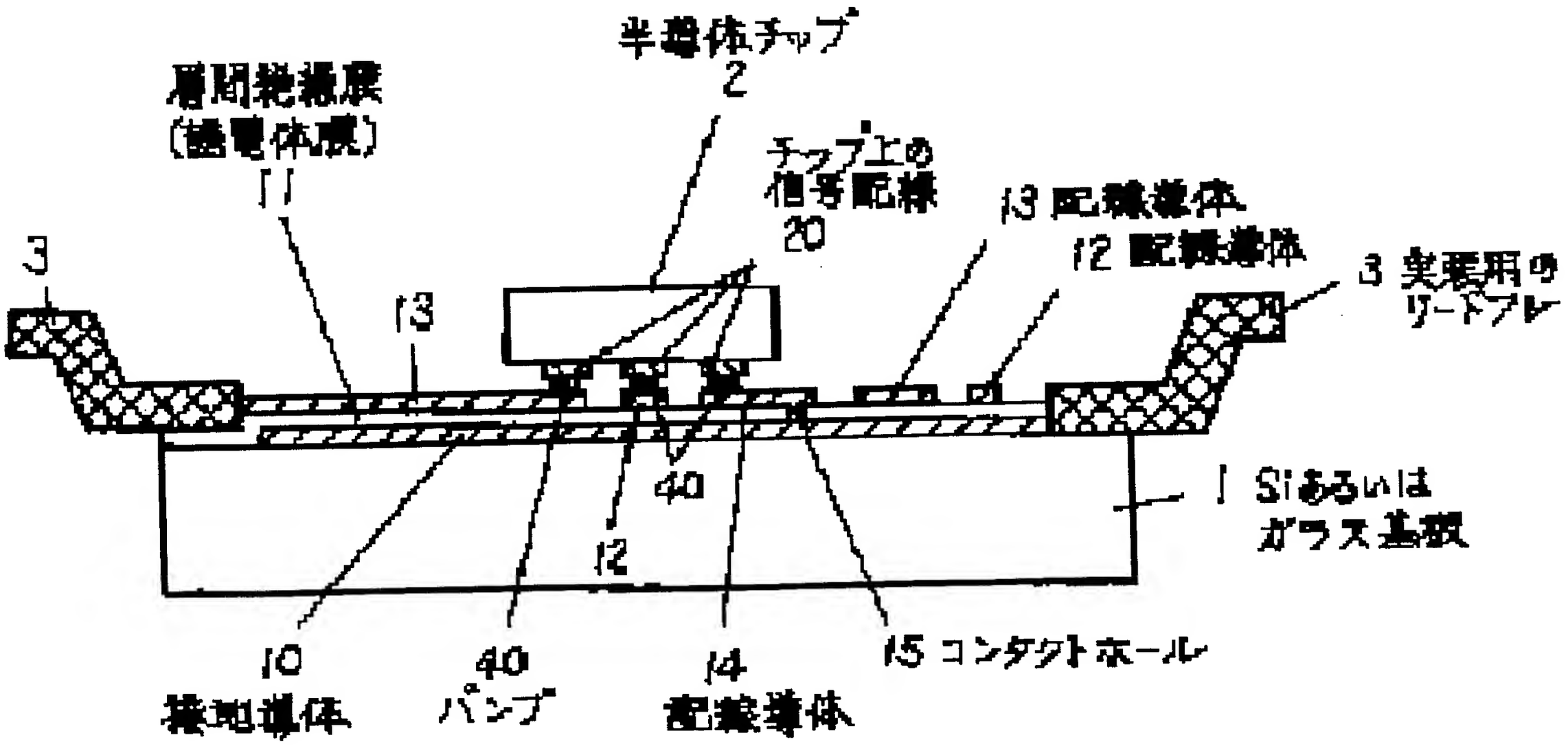
TI - SEMICONDUCTOR DEVICE

AB - PURPOSE:To realize a high performance submilimeter-millimeter wave semiconductor integrated circuit device having large application at low cost.

- CONSTITUTION:A ground conductor10, an interlayer insulation film 11, wiring conductors 12-14, and a contact hole 15 connecting the wiring conductor 14 and the ground conductor 10 are formed on a substrate 1 thus realizing a wiring board including a passive element and a transmission line. A semiconductor chip2 formed with a high frequency transistor is flip chip bonded to a microstrip wiring on the wiring board through a signal wiring20 and a bump 40 on the chip 2. This structure easily realizes a highly accurate microstrip wiring using a semiconductor process.

I - H01L23/12 ;H01L21/60 ;H01P3/08 ;H03F3/60

none	none	none


半導体チップ
2
層間絶縁膜
(誘電体膜)
11
チップ上の
信号配線
20
13 配線導体
12 配線導体
3 実装用の
リードフレ
3
13
40
12
1 Siあるいは
ガラス基板
10
接地導体
40
パンプ
14
配線導体
15 コンタクトホール